

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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20V N-Channel MOSFET



SOP-8



Pin Definition:

1. Source	8. Drain
2. Source	7. Drain
3. Source	6. Drain
4. Gate	Drain

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	20	V
R _{DS(on)} (max)	30	mΩ
Q_g	11.2	nC

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

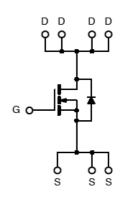
- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM4424CS RLG	SOP-8	2.5Kpcs / 13" Reel
TSM4424CS RVG	SOP-8	3Kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current		I _D	8	Α
Pulsed Drain Current (Note 1)		I _{DM}	30	Α
Continuous Source Current (Diode Conduction)		Is	2.2	Α
Maximum Power Dissipation	Ta = 25°C	P _D	2.5	W
	Ta = 75°C		1.3	
Operating Junction Temperature		T_J	+150	°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance Junction to Foot	$R_{\Theta JF}$	25	°C/W
Thermal Resistance Junction to Ambient	R _{eJA}	52.5	°C/W





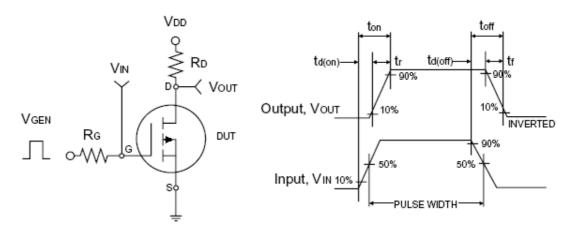
20V N-Channel MOSFET

Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^(Note 2)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$		0.65	1	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
	$V_{GS} = 4.5V, I_D = 4.5A$			23	30	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3.5A$	R _{DS(ON)}		25	35	
	$V_{GS} = 1.8V, I_D = 2.0A$			35	45	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	g _{fs}		40		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}		0.8	1.2	V
Dynamic ^(Note 3)						
Total Gate Charge)/ 40)/ L 45A	Q_g		11.2	14	
Gate-Source Charge	$V_{DS} = 10V, I_D = 4.5A,$ $V_{GS} = 4.5V$	Q_{gs}		1.4		nC
Gate-Drain Charge		Q_{gd}		2.2		
Input Capacitance	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	C _{iss}		500		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		300		рF
Reverse Transfer Capacitance		C_{rss}		140		
Switching ^(Note 4)						
Turn-On Delay Time	$V_{DD} = 10V, \ R_L = 10\Omega,$ $I_D = 1A, \ V_{GEN} = 4.5V,$ $R_G = 6\Omega$	t _{d(on)}		15	25	
Turn-On Rise Time		t _r		30	60	
Turn-Off Delay Time		t _{d(off)}		35	70	ns
Turn-Off Fall Time		t _f		15	45	

Notes:

- 1. Pulse width limited by the maximum junction temperature
- 2. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%
- 3. For DESIGN AID ONLY, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



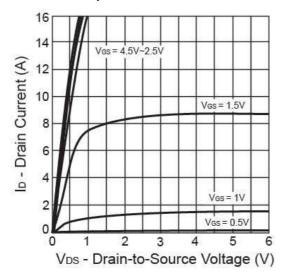
TSM4424

20V N-Channel MOSFET

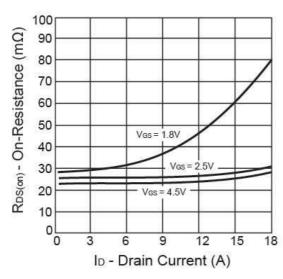
Pb ROHS COMPLIANT

Electrical Characteristics Curve

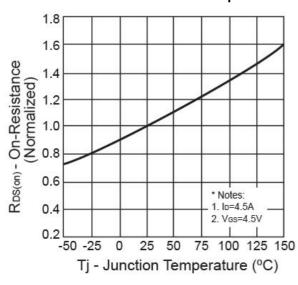
Output Characteristics



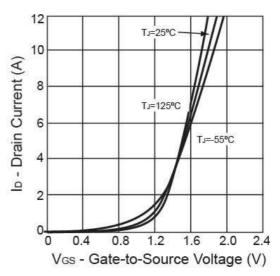
On-Resistance vs. Drain Current



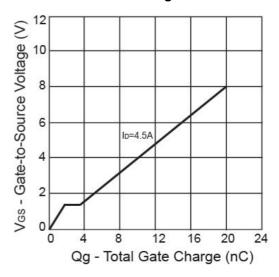
On-Resistance vs. Junction Temperature



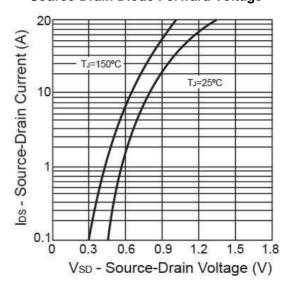
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



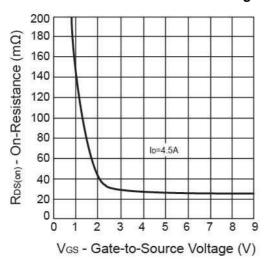
TSM4424

20V N-Channel MOSFET

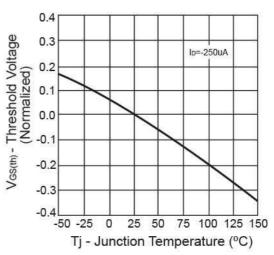


Electrical Characteristics Curve

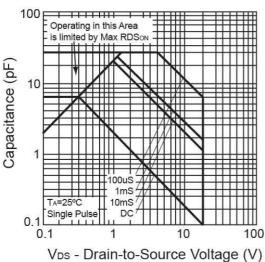
On-Resistance vs. Gate-Source Voltage



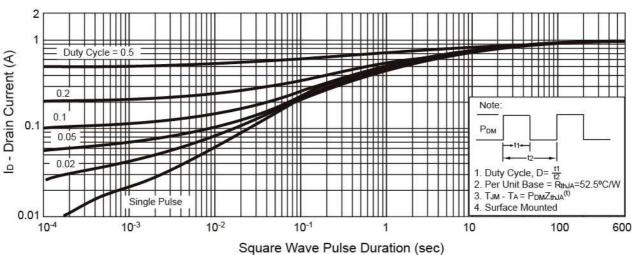
Threshold Voltage



Safety Operation Area



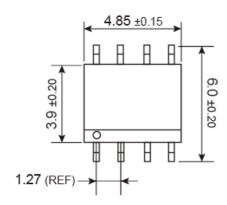
Normalized Thermal Transient Impedance, Junction-to-Ambient

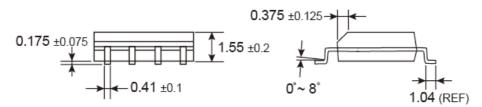






SOP-8 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

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 $oldsymbol{O}$ =Jan $oldsymbol{P}$ =Feb $oldsymbol{Q}$ =Mar $oldsymbol{R}$ =Apr

 $\textbf{S} = \text{May} \quad \textbf{T} = \text{Jun} \quad \textbf{U} = \text{Jul} \quad \textbf{V} = \text{Aug}$

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSM4424 20V N-Channel MOSFET

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